D etection of topological transitions by transport through m olecules and nanodevices

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We analyze the phase transitions of an interacting electronic system weakly coupled to freeelectron leads by considering its zero-bias conductance. This is expressed in terms of two e ective in purity m odels for the cases with and without spin degeneracy. We demonstrate using the halflled ionic H ubbard ring that the weight of the rst conductance peak as a function of external ux or of the di erence in gate voltages between even and odd sites allows one to identify the topological charge transition between a correlated insulator and a band insulator.

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P rogress in nanotechnology has made it possible to perform transport experiments on systems as small as single molecules [1]. M etallic [2] or semiconducting [3, 4, 5] quantum dots (QDs) can now be assembled into articial molecules [4] or solids [2]. QD molecules of different materials and sizes are now being investigated and a wide range of new QD systems is expected to be synthesized in the near future [3, 4]. The transport properties of a nite chain of 15 QDs were rst measured over 10 years ago [5], and the metal-insulator transition has been studied experimentally in a hexagonal lattice of Ag QDs [2]. These advances open the route for new approaches to investigate novel phenomena and theoretical concepts in interacting electron systems.

Here we focus on one such phenom enon, the topological phase transition associated with a parity change of the ground state. The ionic Hubbard model (IHM) with alternating diagonal energy $\frac{1}{2}$ has received much recent attention [6, 7, 8, 9, 10]. It was proposed to describe the neutral-ionic transition in organic charge-transfer salts [11], and later applied to model ferroelectricity in perovskites [6, 12]. At half lling and in the atom ic lim it (t ! 0), the ground state is a band insulator (BI) for U < , but is a M ott insulator (M I) for U > . In one dim ension, with non-zero hopping t, a spontaneously dim erized insulator (SD I) phase appears between B I and MI.W ith increasing U, one nds rst a charge transition at $U = U_c$ from BI to SDI, followed by the closing of the spin gap at $U_s > U_c$, where the transition to the M I occurs. A though in nite systems conventional order param eters such as charge and spin structure factors vary continuously at a phase transition, in a system of L sites one may de ne charge and spin topological num bers which change discontinuously at $U_c(L)$ and $U_s(L)$ [8]. The charge Berry phase has a step at U_{c} (L), where a parity change of the ground state occurs for periodic (antiperiodic) boundary conditions if L = 4m (L = 4m + 2)m integer) [6, 8].

Here we show that this charge transition can be de-



FIG.1: Interacting electron system on a ux-threaded ring, connected by weak links (t^0) to two conducting leads.

The con guration for the proposed experiment is illustrated in Fig. 1. The interacting electron system on the ring is connected to conducting leads through two sites, labeled 0 and n, by weak links with hopping t^0 , and either two materials or two di erent gate voltages at alternating sites may be used to model the IHM . It is essential to distinguish between two cases depending on the spin degeneracy of the isolated interacting system for odd particle num ber. W e thus perform two di erent calculations of the conductance. The rst assumes that spin degeneracy is lifted by a Zeem an interaction, but allows orbital degeneracy of the states, which is important when including interference e ects arising in a ring geometry [13]. In the second, where spin degeneracy is retained, we map the problem into an e ective Anderson m odel (EAM) and express the conductance as a function of the spectral density of the latter.

If the ground state jgi of the interacting system is non-

degenerate, for sm all t^0 the links can be elim inated by a canonical transformation, leading to an elective, non-interacting H am iltonian for the two leads in which the two \impurity" sites i connected to the links (1 and 1 in Fig.1) have an energy shift i (!), and are connected by an elective hopping t_e (!),

$$H_{e} = X_{k_{L}} c_{k_{L}}^{y} c_{k_{L}} + 1 c_{1}^{y} c_{1} + 1 c_{1}^{y} c_{1}$$

$$+ X_{k_{R}} c_{k_{R}}^{y} c_{k_{R}} + X_{k_{R}} c_{1}^{y} c_{1} + H c_{1}^{y} c_{1}$$

$$+ (t_{e} c_{1}^{y} c_{1} + H c_{1}) c_{1}^{y} c_{1}$$

$$+ (t_{e} c_{1}^{y} c_{1} + H c_{1}) c_{1}^{y} c_{1}$$

L (R) refers to the lead containing the site 1 (+1), and the impurity parameters may be expressed in terms of the G reen functions for the isolated ring g_{ij} (!) = hc_i ; c_j^v ii,

The transmittance of H_e may be calculated in different ways. W ithout a ecting the essential results, we assum e identical leads and, for their states without sites (1;1), we consider two models for the density of states (!) and the hybridization V_i (!) with sites (1;1). I) (!) and V_j (!) constant: for j = $1 \text{ and } t_{e} = 0,$ j+i) with = V². II) Leads de $g_{11}^{e_{0}}(!) = 1 = (!)$ scribed by a tight-binding model with nearest-neighbor hopping t, where $g_{jj}^{e_{0}}(!) = 1 = (! = 2)$ j+i(!))with $(!) V^{2} (!) =$ t^2 $!^2=4$. By introducing an (!) =integer m = 1 or 2 for cases I and II,

$$T (!; V_g) =$$
 (3)
 $4^{-2} (!) j_e j^2$

$$\frac{1}{j(\frac{1}{m} + i(!))(\frac{1}{m} + i(!)) + i(!)};$$

 V_{α} is a gate voltage which changes the on-site energy of all sites of the ring by eV_{α} . In case II this equation is exact (8 t^0) in the non-interacting system , and generalizes a previous result [13]. Eq. (3) also generalizes previous approaches in which only one intermediate state of the ring is included [14, 15], and is appropriate for the study of interference e ects [13]. Spin degeneracy lim its its validity to magnetic elds B for which the Kondo e ect is destroyed, as discussed below. For su ciently large Zeem an energy g $_{\rm B}$ B, the zero-bias conductance at steady state is given by $G = G_0 T$ (; V_q)=2, where $G_0 = 2e^2 = h$ is the chem ical potential of the leads. The reand sults of R ef. [16] suggest that Eq. (3) rem ains valid, with $G = G_0 T$ (; V_q), also in the absence of Zeem an splitting in an intermediate temperature range $T_1 < T < 0:1w$, where T_1 is very small. Henceforth we set = 0, corresponding to half-lled leads.

The transmittance as a function of gate voltage is very small except at the poles of g_{n0} . If the ground state gin has N particles for = 0, the ground-state energy $E_q(N)$ satisfies $E_q(N) = V_q < E_q(N)$ and $E_q(N) + V_q < E_q(N)$



FIG. 2: Conductance as a function of gate voltage for the EAM at several magnetic elds. Circles correspond to the conductance of a resonant level for the majority spin only.

 $eV_g < E_g (N + 1)$. As V_g is increased, a pole in $g_{n0} (V_g)$ is reached, and for larger V_g the ground state has N + 1 particles. Sim ilarly, if V_g is lowered, a pole is reached when $z = eV_g + E_g (N - 1)$ $E_g (N) = 0$.

A ssum ing that the state of low est energy for N 1 particles, \dot{g} (N 1) i, is not degenerate, g_j m ay be expressed as a Laurent expansion around z = 0,

$$g_{ij}(z) = \frac{a_i a_j}{z} + _{ij} + _{ij} z + \dots,$$
 (4)

where jj, jj, ::: are real coe cients and

$$a_{j} = hg(N \quad 1)jg jg(N)i:$$
 (5)

 $j = ja_j f$ is the spectral weight for a local photoem ission process. Substituting these expressions in Eqs. (2) and (3), retaining terms to low est nontrivial order in t⁰= (0), and using that T (z) 0 (1) for z. (t⁰)²= (0), yields

$$T(z) = \frac{1}{1 + (w=z)^2} \frac{4_0 n}{(0 + n)^2} + O((t^0 = (0))^2); \quad (6)$$

where the half-width at half maximum peak height is

$$w = (_0 + _n)(t^0)^2 = (0)$$
: (7)

U sing $G = G_0 T$ (; V_g), this expression coincides at su ciently low temperatures with Eq. (7) of Ref. [15].

If sites 0 and n are equivalent by symmetry, then w = $2(t^0)^2_{0} = (0)$ and the integrated weight I = dzT(z) = w are both proportional to $(t^0)^2$ and to $_0$. If V_g is increased instead of decreased, the same result is obtained with $c_j \ ! \ c_j^V$ and N 1 ! N + 1 in Eq. (5). Thus a single transport measurement gives simultaneous spectral information related to photoem ission and to inverse photoem ission. We stress that this information is obtained with much ner energetic resolution (eV) than that available by direct spectroscopic techniques (meV).

We turn next to a calculation of the conductance for small or zero B, where either $j_2(\mathbb{N})$ i or $j_2(\mathbb{N})$ 1) i is spin-degenerate. This degeneracy can be taken into account accurately if w is small compared to the separation between groups of spin-degenerate energy levels, because the problem becomes equivalent to an EAM . For simplicity we take V_g such that a nondegenerate state jg(N) is close in energy to the spin-degenerate state jg(N - 1)i, but extension to other cases is straightforward. Neglecting other states, the EAM for any interacting system between the leads is

$$H_{A} = \begin{array}{cccc} X & X \\ t & c_{i}^{y} c_{i 1} \\ & & d^{y} t^{0} c_{1} c_{1} + t_{1}^{0} c_{1} + H c. \\ & & & & \\ & & & \\ & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & & & \\ & & &$$

$$\begin{split} & \text{with } n_d = d^y d \text{, } t^0_1 = t^0 a_0 \text{, } t^0_1 = t^0 a_n \text{, } "_d = E_g (N) \\ & E_g (N \quad 1) \quad \text{eV} \text{, and in nite } U_A \text{ (justiled because } U_A = \\ & E_g (N) + E_g (N \quad 2) \quad 2E_g (N \quad 1) \text{ w} \text{).} \end{split}$$

The conductance is given by

$$G = \frac{2e^2}{h} \frac{2 w j_1^0 t_1^0 j_1^2}{j_1^0 j_1^2 + j_1^0 j_1^2} X_{d} ();$$
(9)

where d (!) is the spectral density of the elective d electrons [17]. The conductance of the EAM computed as a function of gate voltage for several values of B using slave bosons in the mean-eld approximation (SBM FA) [19] is shown in Fig. 2. For B = 0, G increases abruptly from 0 to G_0 when z 0, and remains nearly perfect for higher V_q due to pinning of the K ondo peak in $_d$ (!) at the Ferm i level. How ever, because the K ondo energy scale T_K decreases exponentially with V_q , even for very small B the plateau becom es a broad peak, term inated when $T_K < g_B B$, beyond which G falls to zero. The abruptness of the fall is an artifact of the SBM FA, but the totalwidth of the feature is well described. For larger B the peak width decreases, tending to w to recover the previous result: for $g_B B \& w$, $G = G_0 T(z)=2$, with T(z) given by Eq. (6).

W e now apply these results to the topological charge transition in the IHM , which is de ned by

$$H_{IHM} = {}^{X}_{b} (C_{i+1}^{y} C_{i} e^{i = L} + H c;) \frac{1}{2} (1)^{i} n_{i}$$

$${}^{i}_{i} X X X^{i}$$

$$g_{B}B (n_{i''} n_{i\#}) + U n_{i''} n_{i\#}; (10)$$

$${}^{i}_{i} i^{i}_{i}$$

where $n_i = c_i^y c_i$, $n_i = \prod_{n=1}^{P} n_i$, and $N = \prod_{i=1}^{P} n_i$. We calculate T (V_g) by exact diagonalization for the isolated ring with L sites and N = L electrons, with leads attached to two sites of the same energy (=2) in the presence of a magnetic ux (Fig.1), with = 2 = 0. The G reen functions $g_{ij}(V_g)$ are obtained numerically and substituted in Eqs. (2) and (3). We choose L = 8, but similar results are obtained for any L = 4n (L = 4n + 2 with ! +). The qualitative features are independent of the lead position n, with the exception of n = L=2 where the transmittance at = vanishes for



FIG.3: Transm ittance as a function of gate voltage for an 8site IHM ring with leads at sites 0 and 2 for $t_R = 1, t^0 = 0.2$, = 3, and values of U below and above U _c (L = 8) = 4:352.

symmetry reasons. Because H $_{\rm IH\,M}\,$ is invariant under simultaneous particle-hole transform ation and sign change of , we restrict our analysis to eV $_g$ < 0. We set t_R = 1 as the unit of energy unless otherwise stated.

The topological transition is present at any value of t_R . As a basis for our study we consider a realistic ring structure containing 8 QDs with only their lowest levels singly occupied, the centers separated by 200 nm [5], and the param eters U; 1 meV and t_R U=4 (intermediate coupling strength). We rst assume the presence of a strong magnetic eld (B 1 T for a Q D array), in the plane of the ring in order not to alter the threading ux, which destroys the Kondo e ect. Fig. 3 shows the rst peak in $G(V_q)$ at = 3 and for two values of U. For L = 8 and = 3, the topological transition occurs at $U_c = 4:352$. The peak width is parameter-dependent: for U = 5, w is approximately constant with decreasing ux, whereas for U = 4, w decreases and the peak disappears at = 0. If $U < U_{c}$, the ground state $\dot{g}(L)$ i for = 0 is even under re ection through any site (corresponding to aBI), while for U > U_c jg (L) i is odd (M Ior SD I) [8]. For = 0, the low est-energy hole enters the system with the Ferm iwave vector, =2, leaving an orbitally degenerate ground state with L 1 particles, jg (L 1) i. For € 0, this degeneracy is broken and jg (L 1) i is odd under reection through any even site if is negative [18]. As a consequence, for $U < U_c$ the matrix element a_0 [Eq. (5)] vanishes by symmetry, whence G is negligible at = 0. The ux acts as a symmetry-breaking eld, which allows one to follow the rst peak in a continuous manner until it disappears as ! 0.

To dem onstrate that these essential features are not affected by the presence of a K ondo resonance we consider the 8-site ring with parameters (Fig. 4) similar to one experimental realization [5] and B norm alto the ring plane so that the threading ux and Zeem an splitting have the



FIG.4: Transm ittance as a function of V_g for a ring of 8 QD s described by the IHM. The parameters chosen are U = 1 meV, = 3U=4, t = U=4, t⁰=t = 0.2, and g_B = 0.025 meV/T. The curves have been shifted in V_g (cf. lower panel Fig.3) such that their maxim a coincide.

sam e origin. Fig. 4 shows the conductance in this regime, calculated using the EAM in the SBM FA. The disappearance of the feature with decreasing ux remains clear.

The topological transition may now be characterized using $_0$. As shown in Fig. 5 for = 3, $_0$ as a function of U (cf. peak widths in Fig. 3 [18]) vanishes discontinuously at U_c for = 0, indicating unambiguously the charge transition. The analogous result obtained for xed U by varying is of direct experimental interest, because can be controlled by a di erence in gate voltage applied between even and odd sites. A nite ux acts as a parity-breaking perturbation and sm ooths the transition. This is the situation for arti cial arrays of QDs, in which perfect structural symmetry is di cult to attain. We note that curves for all ux values cross approxim ately at the sam e point: transport m easurem ents under di erent applied elds can therefore help to locate the transition, even in the absence of perfect re ection sym metry. However, for a smallm olecule, which by de nition exhibits the ! 0 limit, the only source of asymmetry is the leads.

In sum m ary, we have considered the transport properties of a ring-shaped interacting system connected weakly to conducting leads. The conductance is expressed in term softhe spectral density of an EAM, which illustrates the breaking of the K ondo e ect by an applied eld. Outside the K ondo regim e we have derived a transm ittance formula including nontrivial interference e ects. The conductance peaks may be characterized by their total weight, o ering spectral inform ation with far higher resolution than conventional spectroscopic measurements. As an application of this result, we have demonstrated that the conductance can be used to detect the charge transition of m olecules or quantum dot rings described by the IHM . The method is relevant in the general context of systems presenting phase transitions which involve a symmetry change of the ground state.

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FIG. 5: Matrix element $_0$ as a function of U for = 3 (U $_{\rm c} = 4:352$) over a range of values of the ux .

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